Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

HA92

HIGH VOLTAGE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……625mW

V_{CBO}——Collector-Base Voltage……-300V

V_{CEO}——Collector-Emitter Voltage……-300V

V_{EBO}——Emitter-Base Voltage……-5V

I_C——Collector Current……-500mA

TO-92

1—Emitter，E
2—Base，B
3—Collector，C

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-300			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-300			V	I_C=-1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-100μA，I_C=0
I_{CBO}	Collector Cut-off Current			-250	nA	V_{CB}=-200V, I_E=0
I_{EBO}	Emitter-Base Cut-off Current			-100	nA	V_{EB}=-3V, I_C=0
I_{CES}	Collector Cut-off Current			-100	nA	V_{CE}=-300V, V_{BE}=0
H_{FE}（1）	DC Current Gain	25				V_{CE}=-10V, I_C=-1mA
H_{FE}（2）		40				V_{CE}=-10V, I_C=-10mA
H_{FE}（3）		50				V_{CE}=-10V, I_C=-30mA
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			-0.5	V	I_C=-20mA, I_B=-2mA
$V_{CE(sat2)}$				-1	V	I_C=-60mA, I_B=-6mA
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			-0.9	V	I_C=-20mA, I_B=-2mA
f_T	Current Gain-Bandwidth Product	50			MHz	V_{CE}=-20V, I_C=-10mA F=100MHz